P-Channel Enhancement Mode Power MOSFET

Description

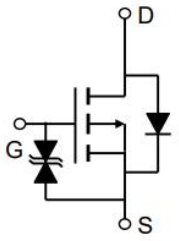
The G1K1P10TE uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge. It can be used in a wide variety of applications.

General Features

- V_{DS} -100V
- I_D (at V_{GS} = -10V) -24A
- $R_{DS(ON)}$ (at V_{GS} = -10V) < 110mΩ
- $R_{DS(ON)}$ (at V_{GS} = -4.5V) < 120mΩ
- 100% Avalanche Tested
- RoHS Compliant
- ESD (HBM) : 7.0KV

Application

- Power switch
- DC/DC converters



Schematic diagram



TO-220

Ordering Information

Device	Package	Marking	Packaging
G1K1P10TE	TO-220	G1K1P10	50pcs/Tube

Absolute Maximum Ratings T_C = 25ºC, unless otherwise noted

Parameter		Symbol	Value	Unit
Drain-Source Voltage		V_{DS}	-100	V
Continuous Drain Current	T_C = 25ºC	I_D	-24	A
	T_C = 100ºC		-15	
Pulsed Drain Current (note1)		I_{DM}	-96	A
Gate-Source Voltage		V_{GS}	±20	V
Power Dissipation		P_D	88	W
Single pulse avalanche energy （note2）		E_{AS}	42	mJ
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 To 150	ºC

Thermal Resistance

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Ambient	R_{thJA}	55	ºC/W
Maximum Junction-to-Case	R_{thJC}	1.42	ºC/W

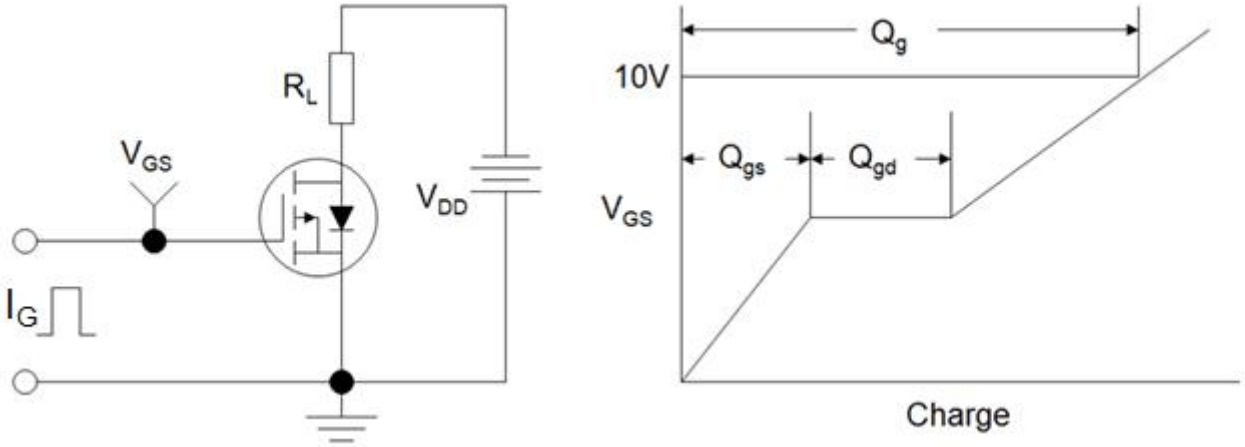
Specifications T_J = 25ºC, unless otherwise noted

Parameter	Symbol	Test Conditions	Value			Unit
			Min.	Typ.	Max.	
Static Parameters						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D = -250μA	-100	--	--	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = -100V, V_{GS} = 0V	--	--	-1	μA
Gate-Source Leakage	I_{GSS}	V_{GS} = ±20V	--	--	±10	uA
Gate-Source Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = -250μA	-1.0	-1.8	-2.5	V
Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS} = -10V, I_D = -15A	--	94	110	mΩ
		V_{GS} = -4.5V, I_D = -15A	--	103	120	
Forward Transconductance	g_{FS}	V_{DS} = -15V,I_D = -15A	--	35	--	S
Dynamic Parameters						
Input Capacitance	C_{iss}	V_{GS} = 0V, V_{DS} = -50V, f = 1.0MHz	--	3300	--	pF
Output Capacitance	C_{oss}		--	91	--	
Reverse Transfer Capacitance	C_{rss}		--	90	--	
Total Gate Charge	Q_g	V_{DD} = -50V, I_D = -15A, V_{GS} = -10V	--	65	--	nC
Gate-Source Charge	Q_{gs}		--	10	--	
Gate-Drain Charge	Q_{gd}		--	14	--	
Turn-on Delay Time	$t_{d(on)}$	V_{DD} = -50V, I_D = -15A, R_G = 9Ω	--	16	--	ns
Turn-on Rise Time	t_r		--	73	--	
Turn-off Delay Time	$t_{d(off)}$		--	34	--	
Turn-off Fall Time	t_f		--	57	--	
Drain-Source Body Diode Characteristics						
Continuous Body Diode Current	I_S	T_C = 25ºC	--	--	-24	A
Body Diode Voltage	V_{SD}	T_J = 25ºC, I_{SD} = -15A, V_{GS} = 0V	--	--	-1.2	V
Reverse Recovery Charge	Q_{rr}	I_F = -15A, V_{GS} = 0V di/dt=-500A/us	--	66	--	nC
Reverse Recovery Time	T_{rr}		--	88	--	ns

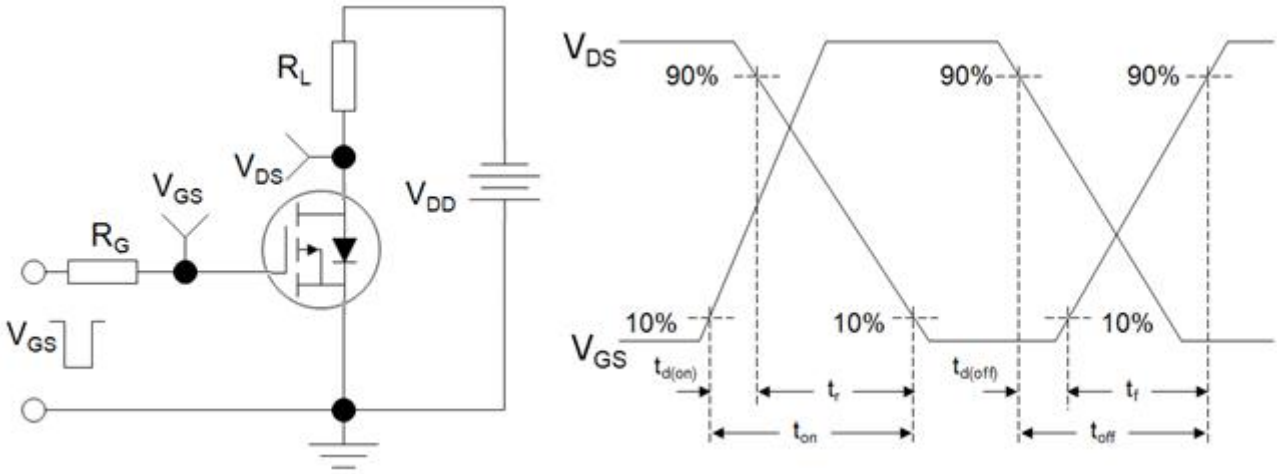
Notes

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. EAS condition : Tj=25℃ ,VDD=-50V,VGS=-10V,L=0.5mH,Rg=25Ω
   The table shows the minimum avalanche energy, which is 110mJ when the device is tested until failure
3. Identical low side and high side switch with identical R_G

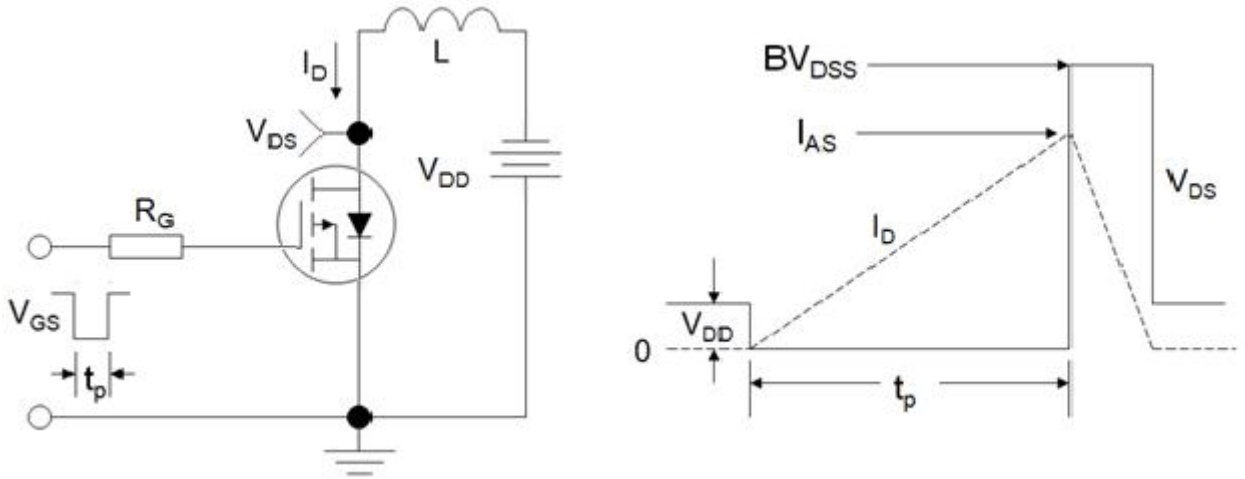
Gate Charge Test Circuit



Switch Time Test Circuit



EAS Test Circuit



Typical Characteristics T_J = 25ºC, unless otherwise noted

Figure 1. Output Characteristics

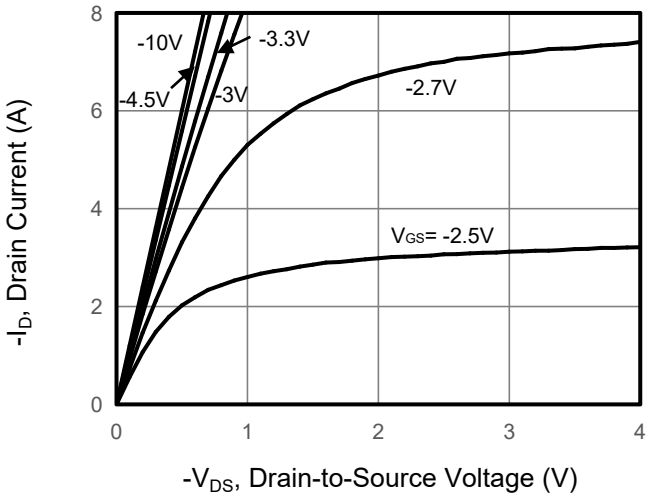


Figure 2. Transfer Characteristics

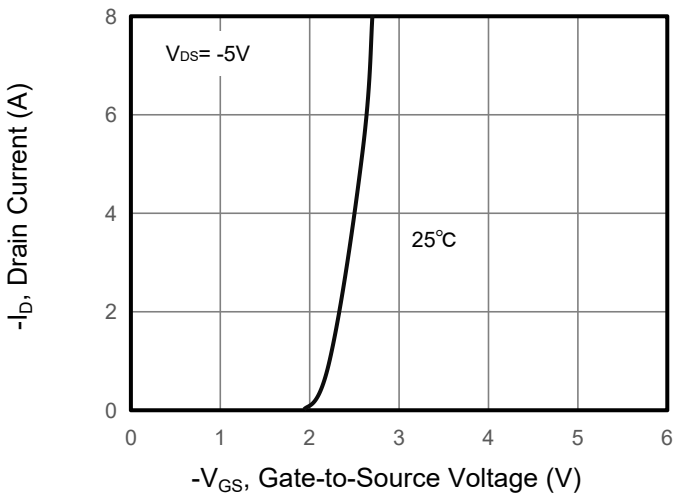


Figure 3.Drain Source On Resistance

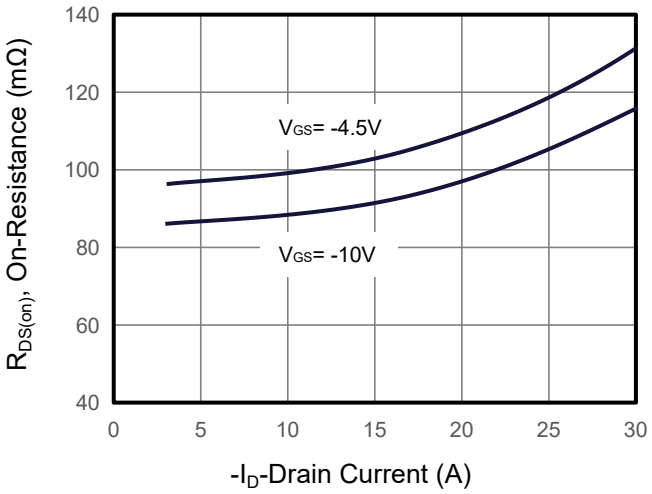


Figure 4. Gate Charge

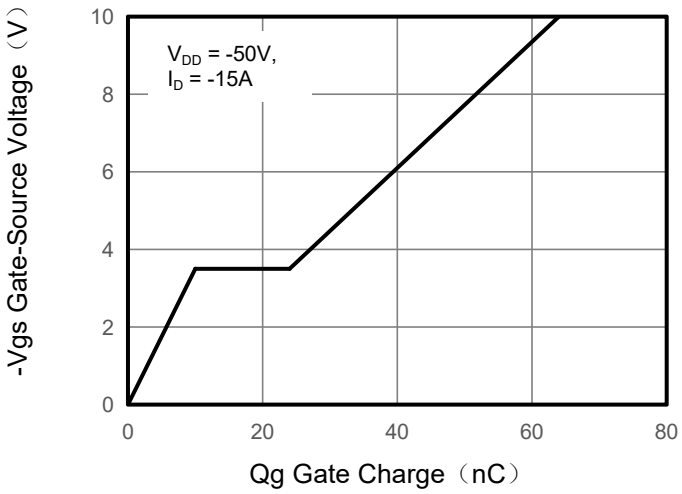


Figure 5. Capacitance

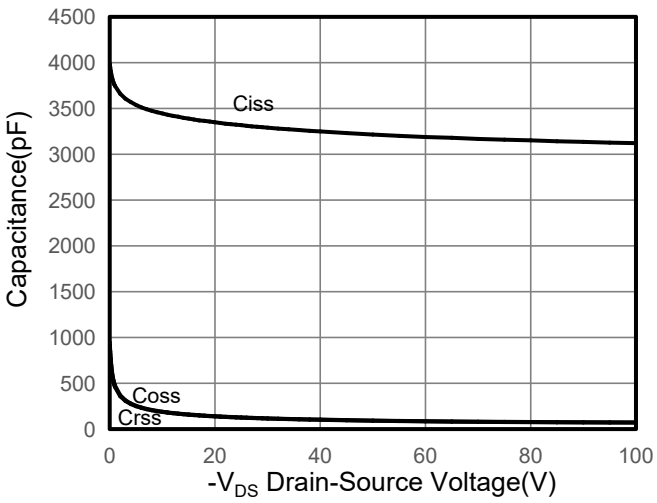
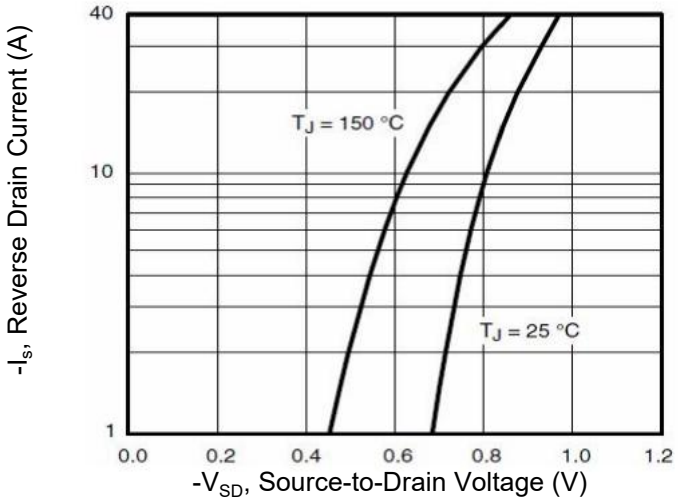


Figure 6. Source-Drain Diode Forward



Typical Characteristics T_J = 25ºC, unless otherwise noted

Figure 7. Drain-Source On-Resistance

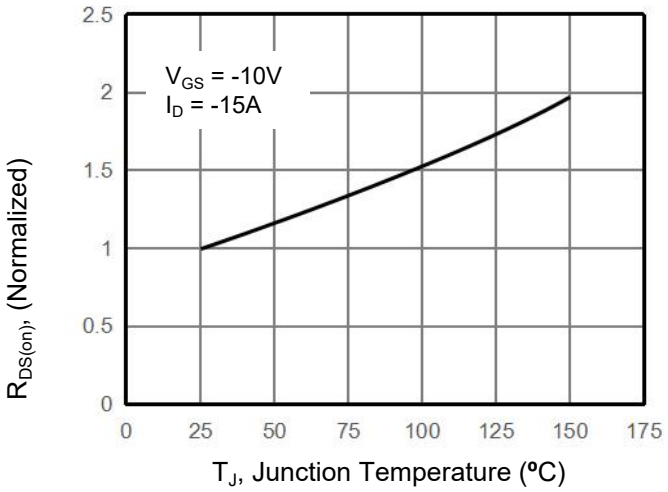


Figure 8. Safe Operation Area

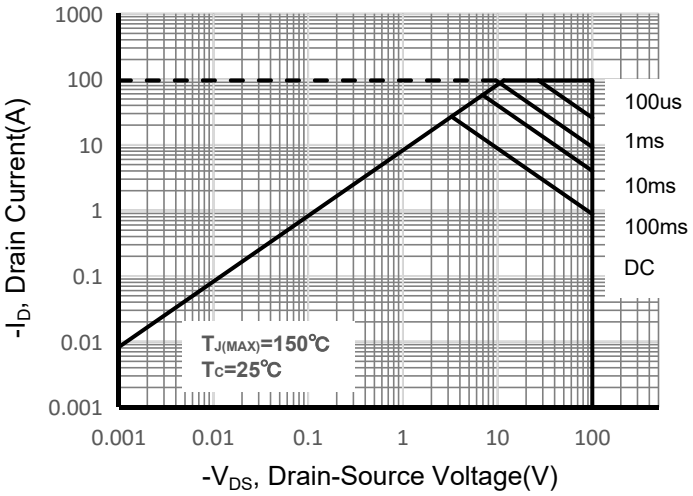


Figure 9. Maximum Continuous Drain Current vs Case Temperature

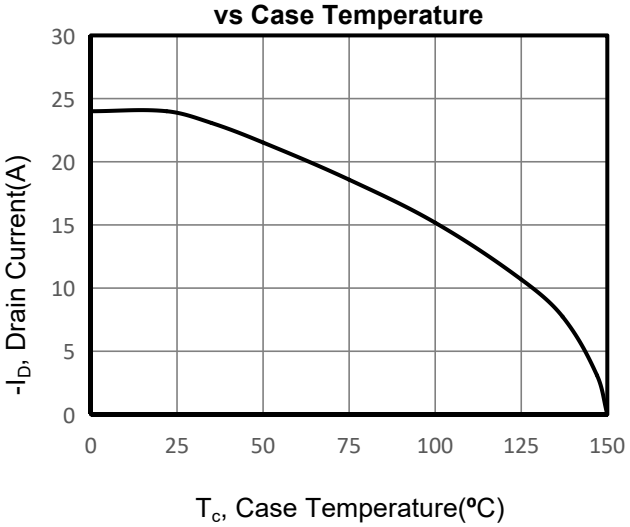
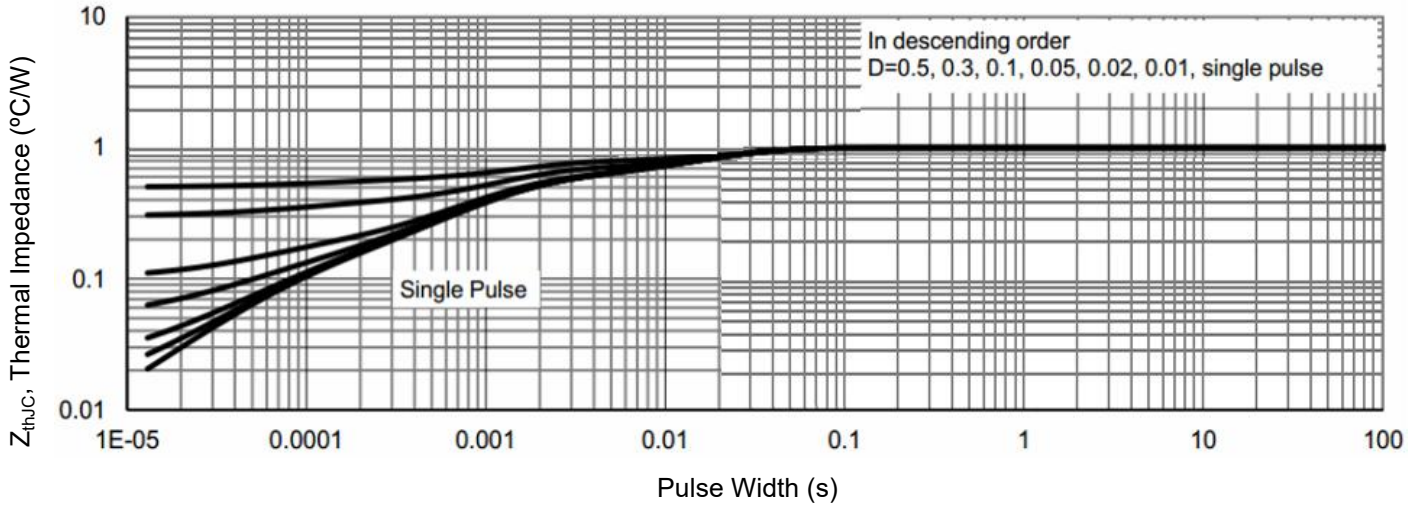
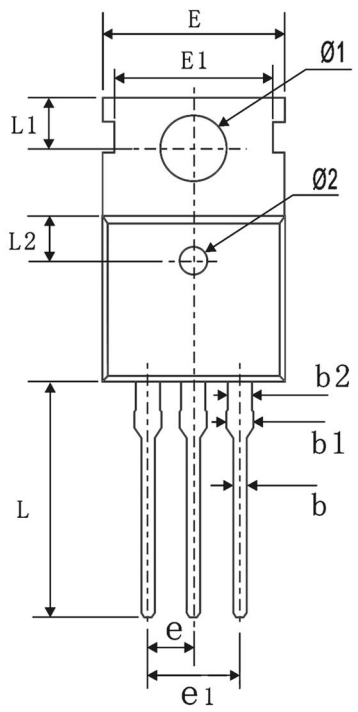


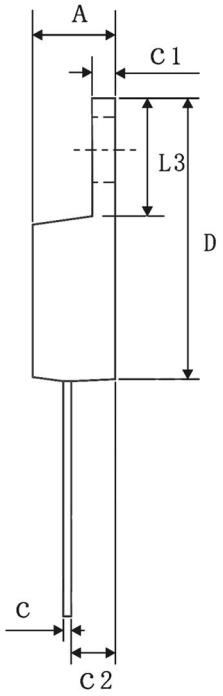
Figure 10. Normalized Maximum Transient Thermal Impedance



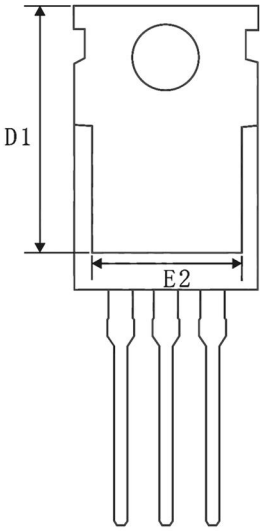
TO-220 Package Information



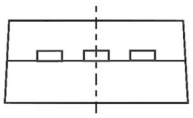
TOP VIEW



SIDE VIEW



BOTTOM VIEW



SIDE VIEW

COMMON DIMENSIONS
(UNITS OF MEASURE=mm)

SYMBOL	MIN	NOM	MAX
A	4.30	4.50	4.70
b	0.70	0.80	0.90
b1	——	——	1.42
b2	1.17	1.27	1.37
c	0.40	0.50	0.60
c1	1.25	1.30	1.35
c2	2.20	2.40	2.60
D	15.45	15.65	15.85
D1	13.20	13.40	13.60
E	9.80	10.0	10.2
E1	8.60	8.70	8.80
E2	7.80	8.00	8.20
e1	4.88	5.08	5.28
L	12.95	13.15	13.35
L1	2.70	2.80	2.90
L2	2.40	2.50	2.60
L3	6.30	6.50	6.70
Ø1	3.50	3.60	3.70
Ø2	1.35	1.50	1.65
e	2.54BSC		